

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[STMicroelectronics](#)

[BUL3N7](#)

For any questions, you can email us directly:

sales@integrated-circuit.com



BUL3N7

MEDIUM VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

Features

- MEDIUM VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

Applications

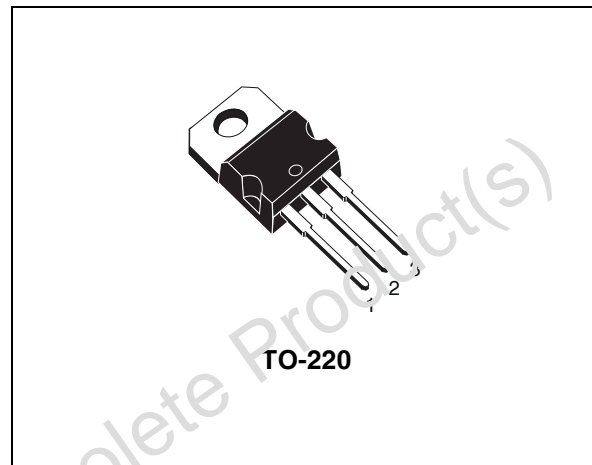
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING

Description

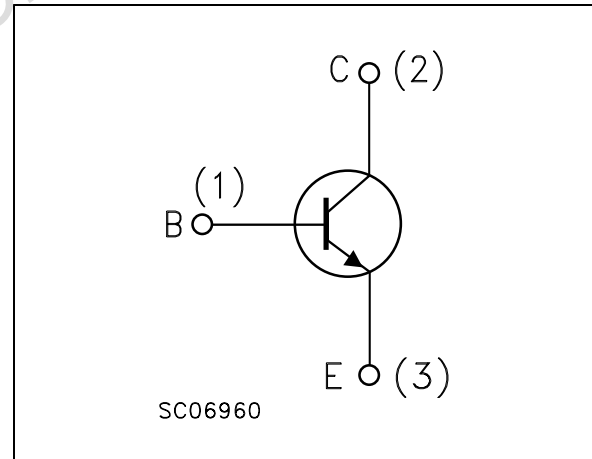
The BUL3N7 is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is expressly designed for a new solution to be used in compact fluorescent lamps, H.F. ballast voltage FL where it is coupled with the BUL3P5, its complementary PNP transistor.



Internal Schematic Diagram



Order Codes

Part Number	Marking	Package	Packing
BUL3N7	BUL3N7	TO-220	TUBE

1 Absolute Maximum Ratings

Table 1. Absolute Maximum Rating

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	700	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0, I_B = -0.75\text{ A}, t_p < 100\text{ms}, T_j < 150^\circ\text{C}$)	$V_{(BR)EBO}$	V
I_C	Collector Current	3	A
I_{CM}	Collector Peak Current ($t_p < 5\text{ms}$)	6	A
I_B	Base Current	1.5	A
I_{BM}	Base Peak Current ($t_p < 5\text{ms}$)	3	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	30	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. Operating Junction Temperature	150	$^\circ\text{C}$

Table 2. Thermal Data

Symbol	Parameter	Value	Unit
$R_{thJ-case}$	Thermal Resistance Junction-Case Max	2.08	$^\circ\text{C/W}$
$R_{thJ-amb}$	Thermal Resistance Junction-Ambient Max	62.5	$^\circ\text{C/W}$

BUL3N7

2 Electrical Characteristics

2 Electrical Characteristics

Table 3. Electrical Characteristics ($T_{CASE} = 25^{\circ}C$; unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 700\text{ V}$			0.1	mA
		$V_{CE} = 700\text{ V}$ $T_C = 125^{\circ}C$			0.5	mA
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 10\text{ mA}$	10		18	V
$V_{CEO(sus)}$ <i>Note: 1</i>	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100\text{ mA}$	400			V
$V_{CE(sat)}$ <i>Note: 1</i>	Collector-Emitter Saturation Voltage	$I_C = 0.7\text{ A}$ $I_B = 0.1\text{ A}$			0.5	V
		$I_C = 1\text{ A}$ $I_B = 0.2\text{ A}$			0.5	V
$V_{BE(sat)}$ <i>Note: 1</i>	Base-Emitter Saturation Voltage	$I_C = 0.5\text{ A}$ $I_B = 0.1\text{ A}$			1.1	V
		$I_C = 1\text{ A}$ $I_B = 0.2\text{ A}$			1.2	V
		$I_C = 2\text{ A}$ $I_B = 0.4\text{ A}$			1.3	V
h_{FE}	DC Current Gain	$I_C = 10\text{ mA}$ $V_{CE} = 5\text{ V}$	10			
		$I_C = 0.7\text{ A}$ $V_{CE} = 5\text{ V}$	18		34	
		$I_C = 2\text{ A}$ $V_{CE} = 5\text{ V}$	4			
t_r t_s t_f	RESISTIVE LOAD Rise Time Storage Time Fall Time	$I_C = 0.7\text{ A}$ $V_{CC} = 250\text{ V}$		80		ns
		$I_{D1} = 0.14\text{ A}$ $I_{B2} = -0.14\text{ A}$		2.4		μs
		$T_p = 30\text{ }\mu\text{s}$		100		ns
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 1\text{ A}$ $I_{B1} = 0.2\text{ A}$		450		ns
		$V_{BE(off)} = -5\text{ V}$ $R_{bb} = 0\text{ }\Omega$ $L = 1\text{ mH}$ $V_{clamp} = 200\text{ V}$		120		ns

Note: 1. Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$.

2.1 Typical Characteristics

Figure 1. Safe Operating Area

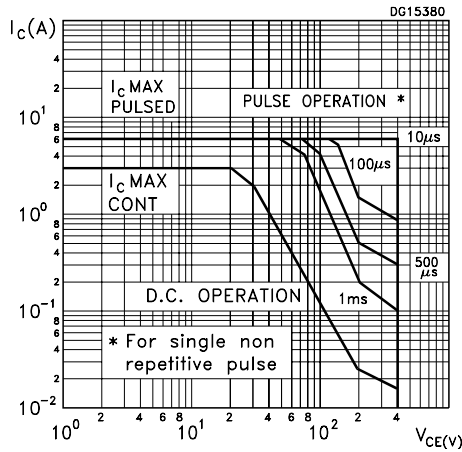


Figure 2. DC Current Gain

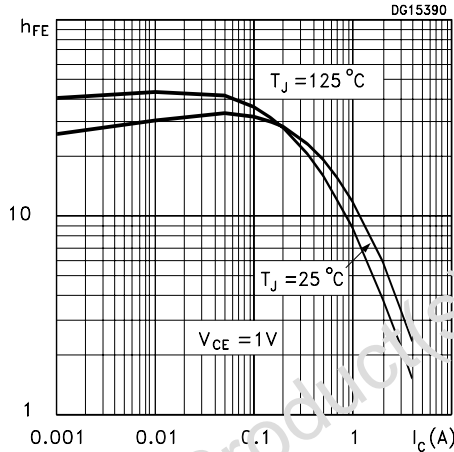


Figure 3. DC Current Gain

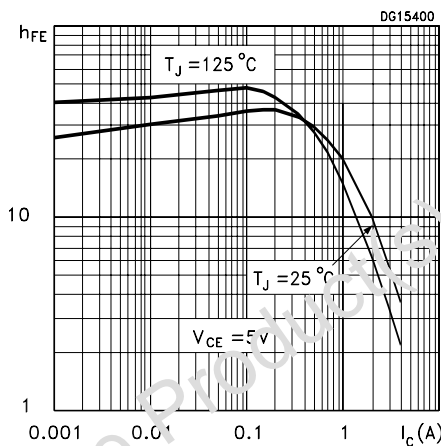


Figure 4. Collector Emitter Saturation Voltage

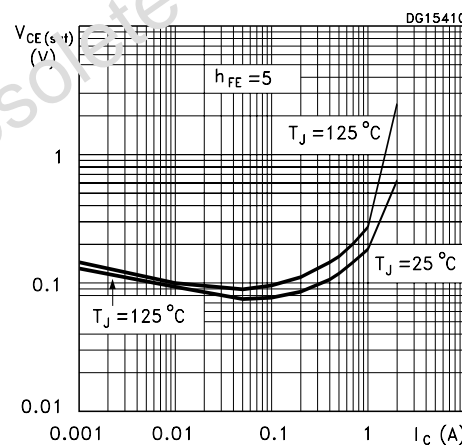


Figure 5. Base Emitter Saturation Voltage

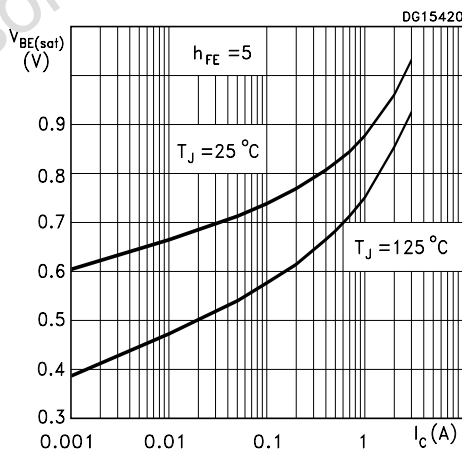
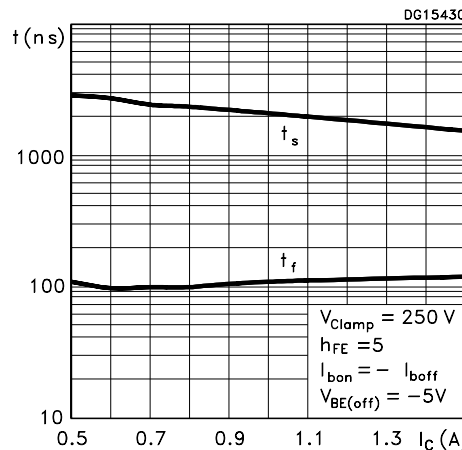


Figure 6. Switching Times Resistive Load



BUL3N7

2 Electrical Characteristics

Figure 7. Switching Times Inductive Load

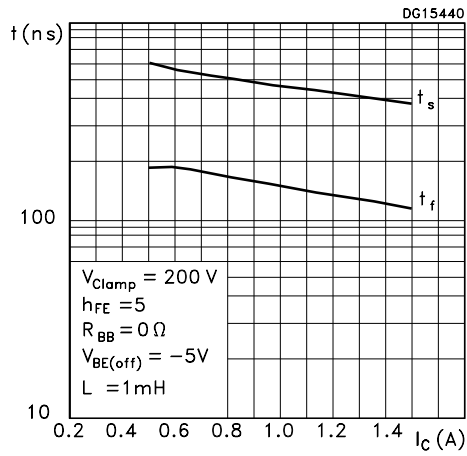
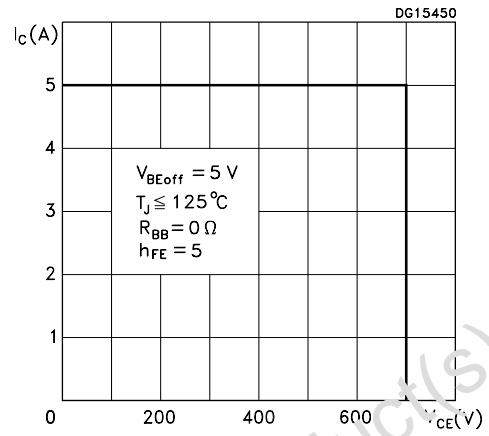


Figure 8. Reverse Biased SOA



Obsolete Product(s) - Obsolete Product(s)

3 Test Circuits

Figure 9. Inductive Load Switching Test Circuit

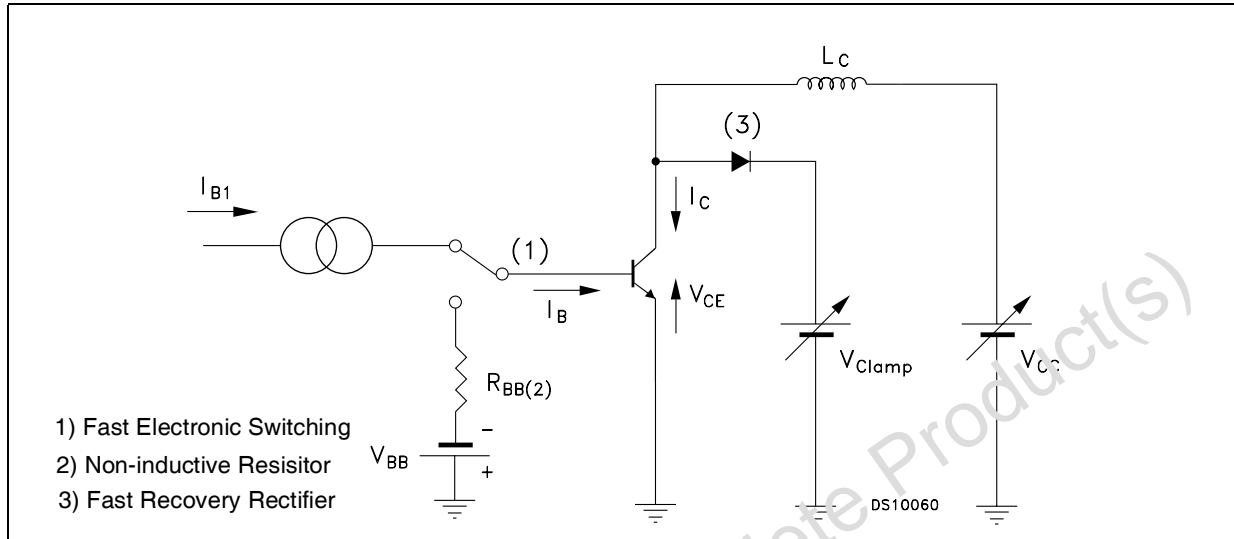
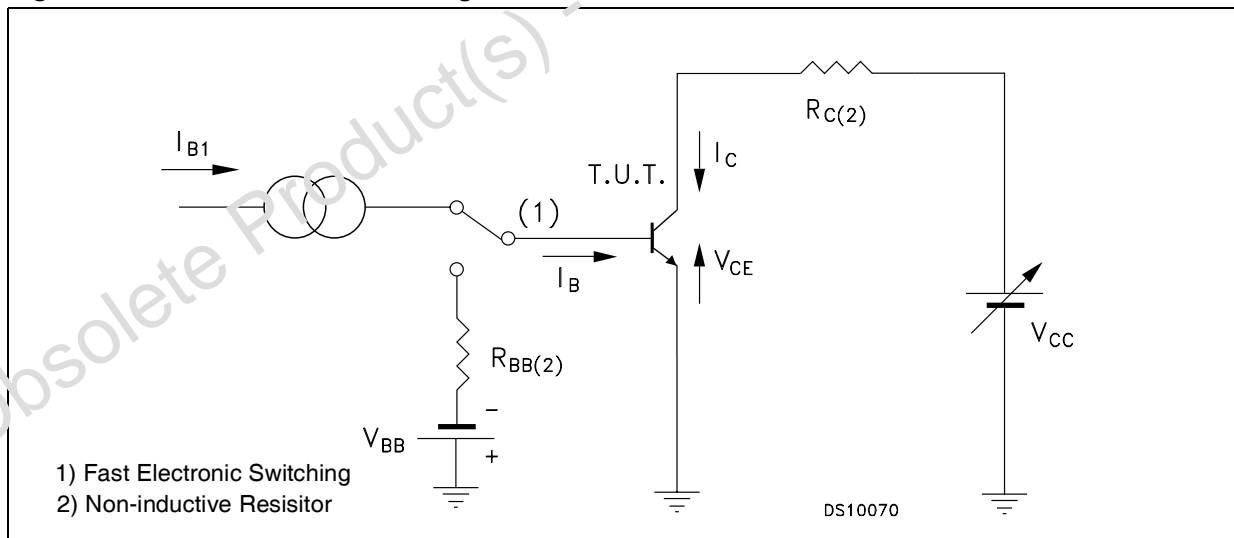


Figure 10. Resistive Load Switching Test Circuits



4 Package Mechanical Data

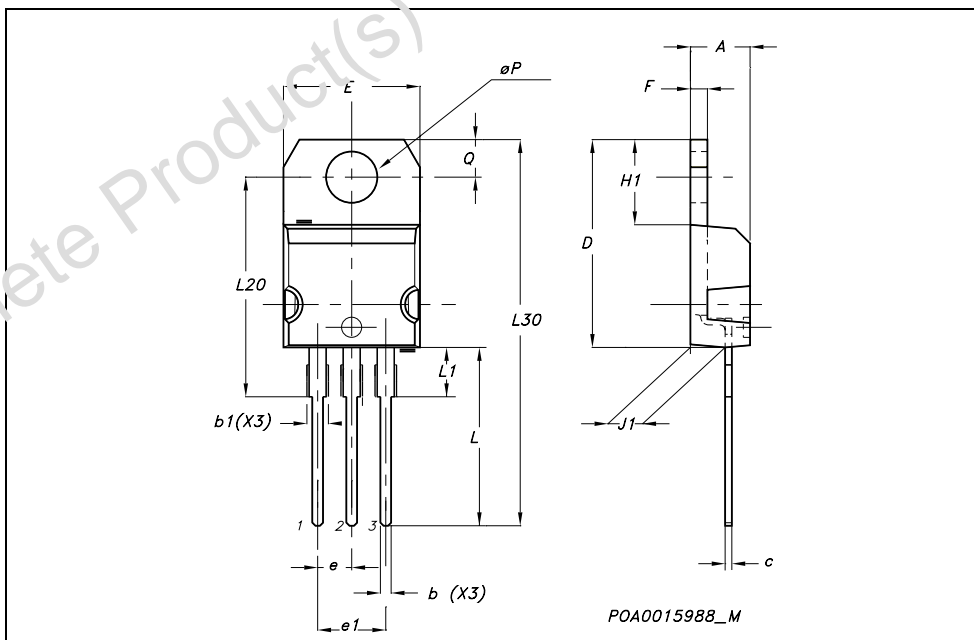
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

4 Package Mechanical Data

BUL3N7

TO-220 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



5 Revision History

Date	Revision	Changes
09-Dec-2005	1	Initial Release

Obsolete Product(s) - Obsolete Product(s)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com